

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-20V	400mΩ@-4.5V	-0.66A
	550mΩ@-2.5V	

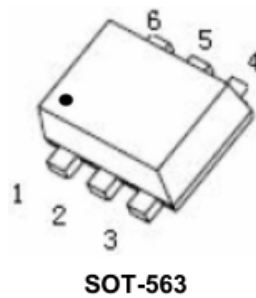
## Feature

- Surface Mount Package
- P-Channel Switch with Low RDS(on)
- Operated at Low Logic Level Gate Drive

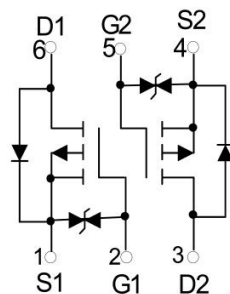
## Applications

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics

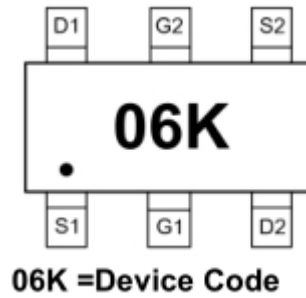
## Package



## Circuit diagram



## Marking



## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Continuous Drain Current	I <sub>D</sub>	-0.66	A
Pulsed Drain Current	I <sub>DM</sub>	-1.2	A
Power Dissipation	P <sub>D</sub>	0.15	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	357	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG.</sub>	-55~ +150	°C

## Electrical characteristics

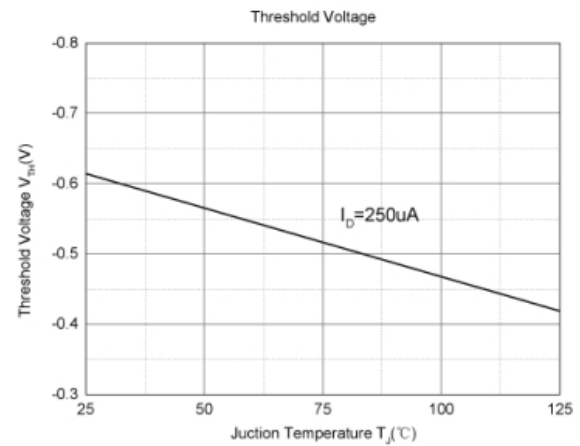
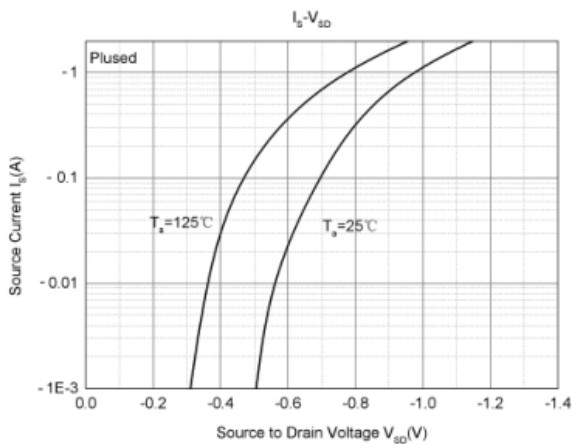
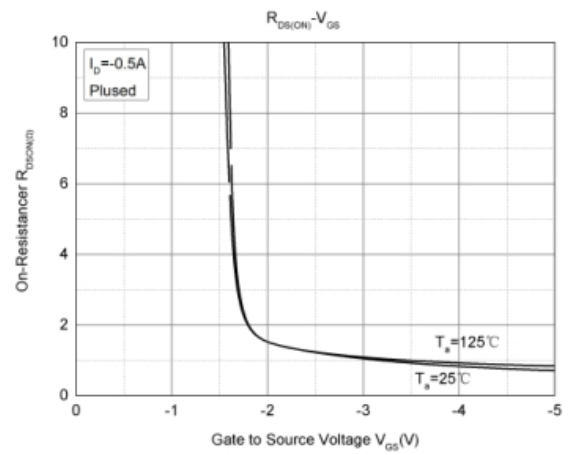
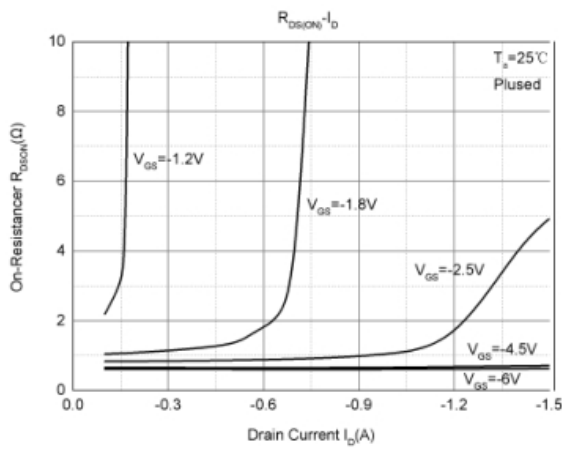
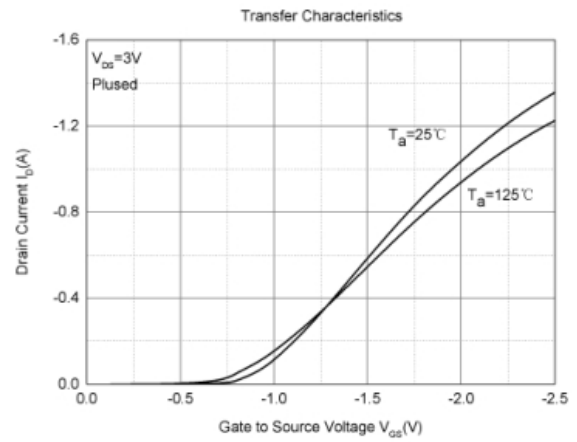
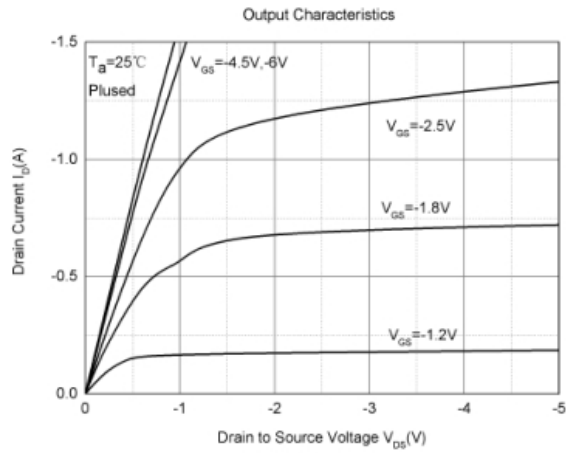
( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V			-1	uA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V			±10	uA
Gate threshold voltage <sup>(1)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.35	-0.65	-1	V
Drain-source on-resistance <sup>(1)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -0.5A		0.65	0.75	Ω
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -0.2A		0.85	1.0	
Dynamic Characteristics						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -16V, V <sub>GS</sub> =0V, f=1MHz		113		pF
Output capacitance	C <sub>oss</sub>			15		
Reverse transfer capacitance	C <sub>rss</sub>			9		
Turn-on Delay Time	T <sub>d(on)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> =200mA , V <sub>GS</sub> = -4.5V, R <sub>GEN</sub> =10Ω		9		nS
Turn-on Rise Time	T <sub>r</sub>			5.7		
Turn-Off Delay Time	T <sub>d(off)</sub>			32.6		
Turn-Off Fall Time	t <sub>f</sub>			20.3		
Source-Drain Diode Characteristics						
Diode Forward voltage	V <sub>SD</sub>	I <sub>S</sub> =-0.5A, V <sub>GS</sub> = 0V			-1.2	V

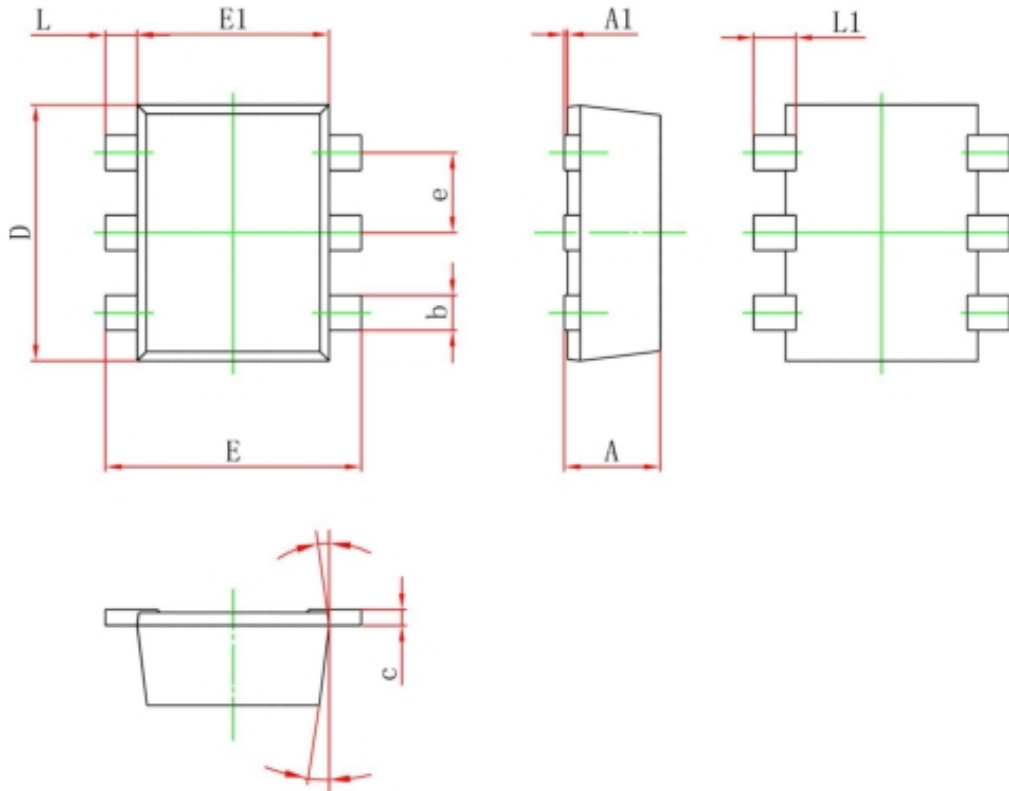
### Notes:

1. Pulse Test: Pulse Width < 300 $\mu s$ , Duty Cycle  $\leq 2\%$ .
2. Guaranteed by design, not subject to production testing.

## Typical Characteristics



## SOT-563 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.525	0.600
A1	0.000	0.050
e	0.450	0.550
c	0.090	0.160
D	1.500	1.700
b	0.170	0.270
E1	1.100	1.300
E	1.500	1.700
L	0.100	0.300
L1	0.200	0.400
θ	7°Ref.	